

TOSHIBA Power Transistor Module
Silicon NPN Triple Diffused Type (Darlington power transistor 4 in 1)

MP4015

High Power Switching Applications.
Hammer Drive, Pulse Motor Drive.
Inductive Load Switching.

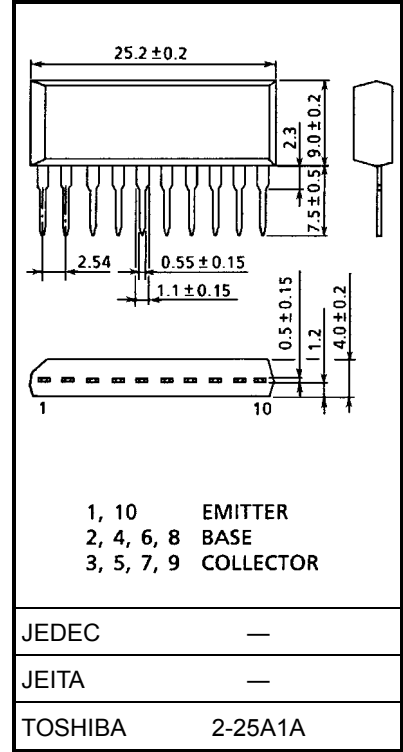
- Small package by full molding (SIP 10 pin)
- High collector power dissipation (4 devices operation)
: $P_T = 4 \text{ W}$ ($T_a = 25^\circ\text{C}$)
- High collector current: I_C (DC) = 5 A (max)
- High DC current gain: $h_{FE} = 1000$ (min) ($V_{CE} = 4 \text{ V}$, $I_C = 3 \text{ A}$)
- Zener diode included between collector and base.
- Unclamped inductive load energy: $E_{S/B} = 100 \text{ mJ}$ (min)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	55	V
Collector-emitter voltage	V_{CEO}	60 ± 10	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	DC	I_C	5
	Pulse	I_{CP}	8
Continuous base current	I_B	0.5	A
Collector power dissipation (1 device operation)	P_C	2.0	W
Collector power dissipation (4 devices operation)	P_T	4.0	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$

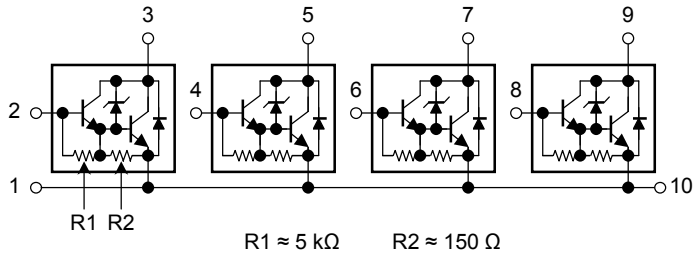
Industrial Applications

Unit: mm



Weight: 2.1 g (typ.)

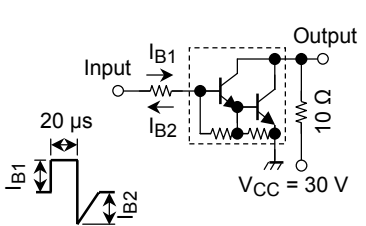
Array Configuration

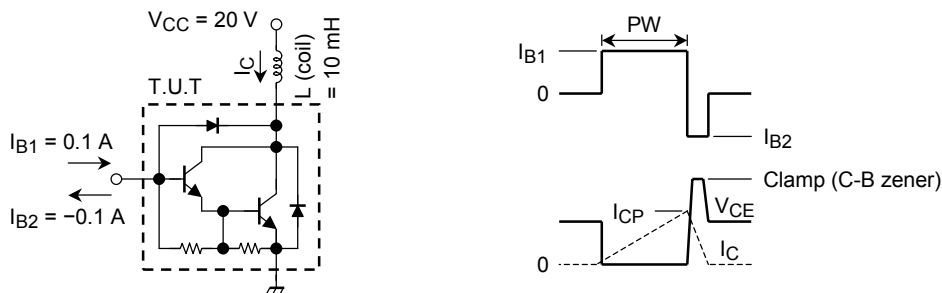


Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance of junction to ambient (4 devices operation, Ta = 25°C)	$\Sigma R_{th(j-a)}$	31.3	°C/W
Maximum lead temperature for soldering purposes (3.2 mm from case for 10 s)	T _L	260	°C

Electrical Characteristics (Ta = 25°C)

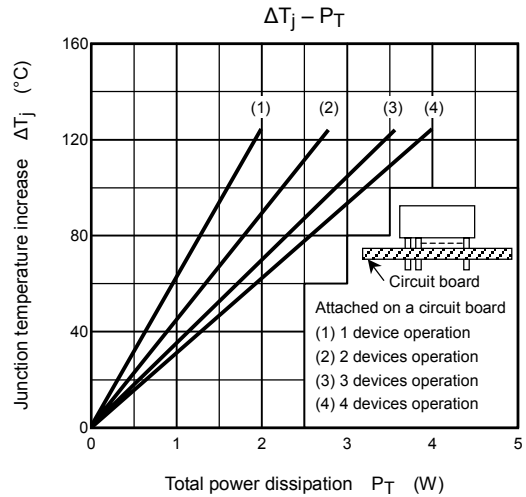
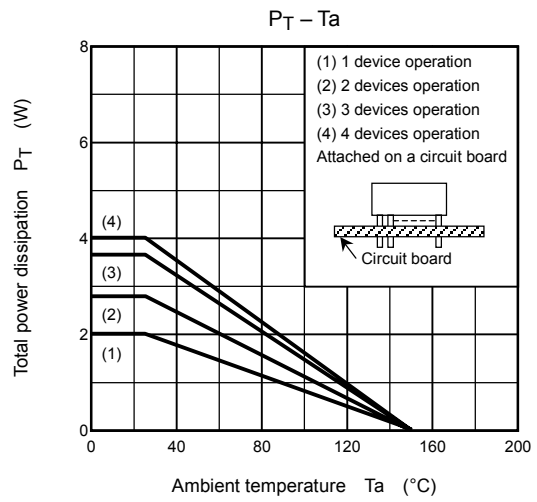
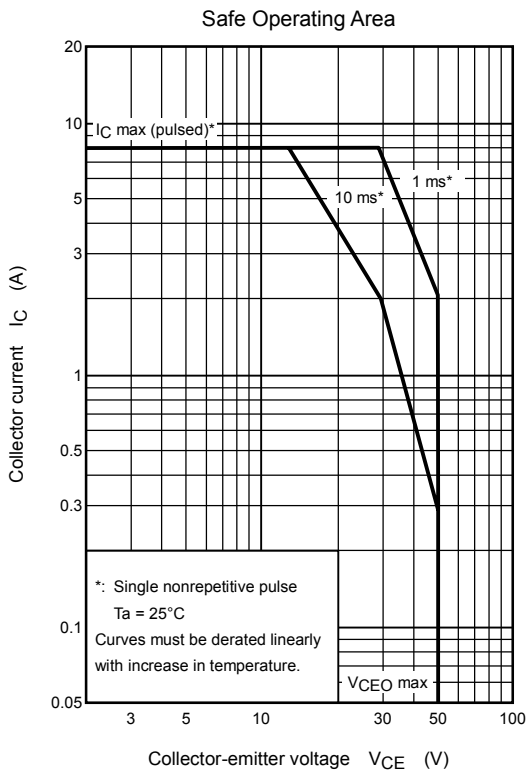
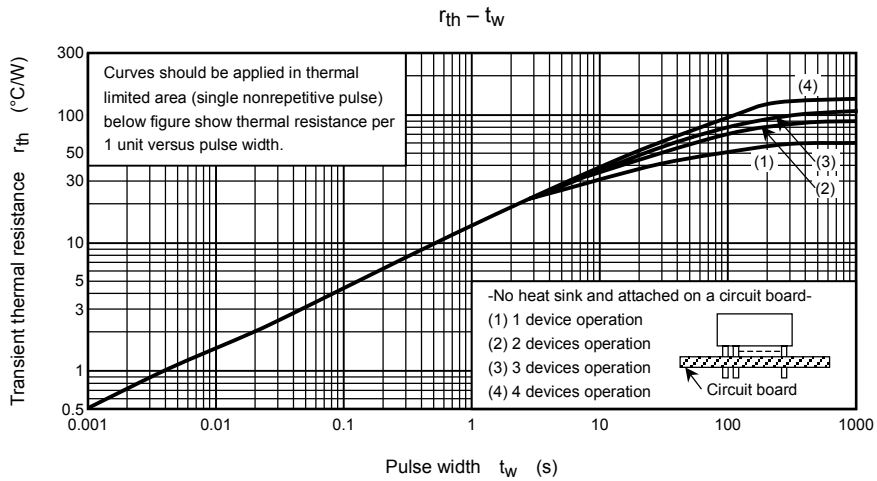
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I _{CBO}	V _{CB} = 45 V, I _E = 0 A	—	—	10	μA
Collector cut-off current		I _{CEO}	V _{CE} = 45 V, I _B = 0 A	—	—	10	μA
Emitter cut-off current		I _{EBO}	V _{EB} = 6 V, I _C = 0 A	0.3	—	10	mA
Collector-base breakdown voltage		V _{(BR)CBO}	I _C = 10 mA, I _E = 0 A	50	—	70	V
DC current gain		h _{FE} (1)	V _{CE} = 4 V, I _C = 1 A	1000	—	—	—
		h _{FE} (2)	V _{CE} = 4 V, I _C = 3 A	1000	—	—	
Saturation voltage	Collector-emitter	V _{CE} (sat) (1)	I _C = 1 A, I _B = 4 mA	—	0.9	1.4	V
		V _{BE} (sat) (2)	I _C = 3 A, I _B = 10 mA	—	1.3	2.0	
Base-emitter	V _{BE} (sat)	I _C = 1 A, I _B = 4 mA	—	1.6	2.0		
Base-emitter voltage		V _{BE}	V _{CE} = 4 V, I _B = 3 A	—	1.8	2.5	V
Transition frequency		f _T	V _{CE} = 3 V, I _C = 0.5 A	—	7	—	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0 A, f = 1 MHz	—	44	—	pF
Switching time	Turn-on time	t _{on}		—	0.6	—	μs
	Storage time	t _{stg}		—	4.2	—	
	Fall time	t _f		—	2.3	—	
Unclamped inductive load energy		E _{S/B}	Refer to Figure 1	100	—	—	mJ



Note 1: Pulse width adjusted for desired I_{CP} (I_{CP} = 4.48 A min)

Note 2: $E_{S/B} = \frac{1}{2} L \cdot I_{CP}^2$

Figure 1 Measurement Circuit of Unclamped Inductive Load Energy E_{S/B}



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